

RJK2057DPA

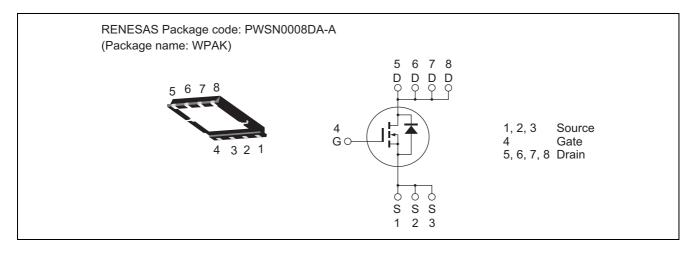
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1761-0300 Rev.3.00 Apr 09, 2009

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	20	A
Drain peak current	I _{D (pulse)} Note1	40	A
Body-drain diode reverse drain current	I _{DR}	20	A
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	40	А
Avalanche current	I _{AP} Note3	9	А
Avalanche energy	E _{AR} Note3	5.4	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

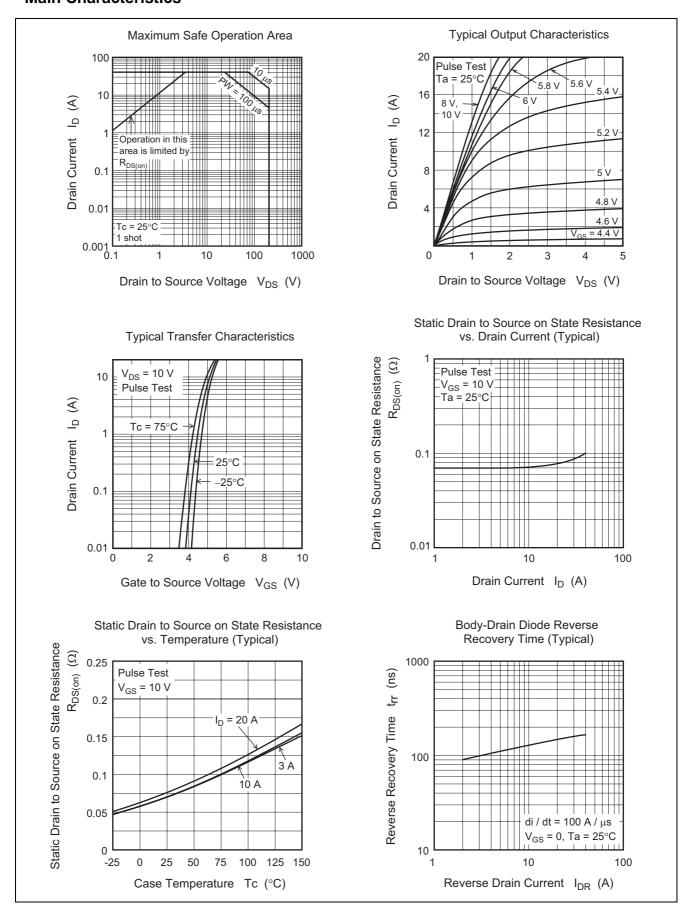
Electrical Characteristics

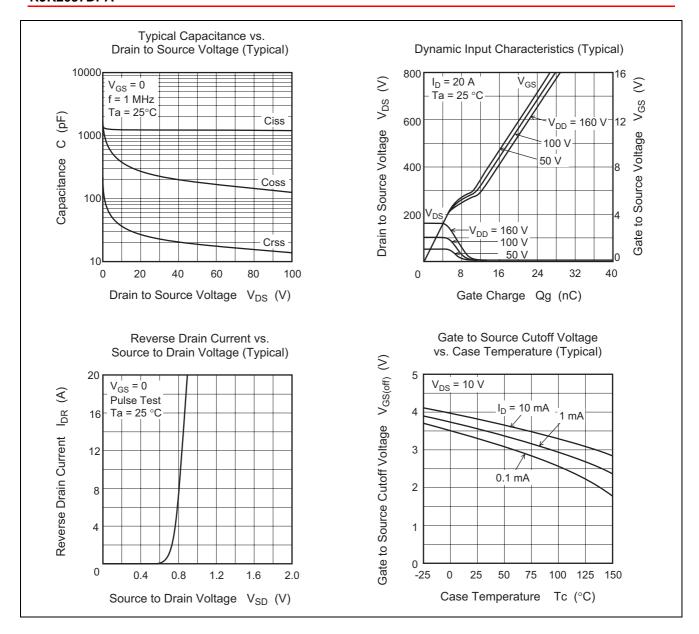
 $(Ta = 25^{\circ}C)$

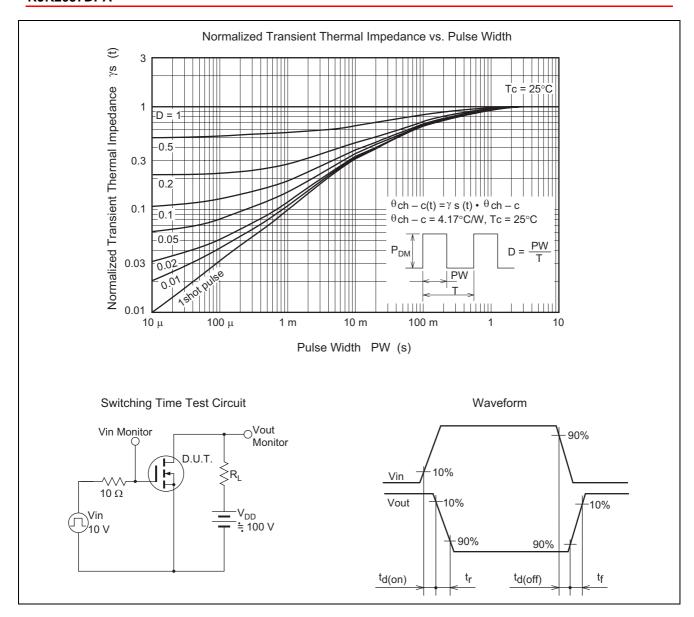
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.068	0.085	Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1250	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	245	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	25	_	pF	
Turn-on delay time	t _{d(on)}	_	23	_	ns	I _D = 10 A
Rise time	t _r	_	46	_	ns	$V_{GS} = 10 \text{ V}$ $R_{L} = 10 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	$t_{d(off)}$	_	35	_	ns	
Fall time	t _f	_	28	_	ns	
Total gate charge	Qg	_	19	_	nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	6.9	_	nC	V _{GS} = 10 V I _D = 20 A
Gate to drain charge	Qgd	_	5.3	_	nC	
Body-drain diode forward voltage	V_{DF}	_	0.90	1.35	V	$I_F = 20 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	145	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

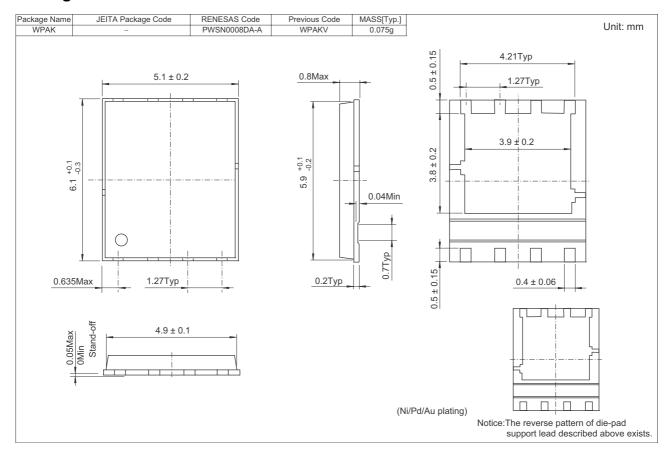
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2057DPA-00-J0	2500 pcs	Taping

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